

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



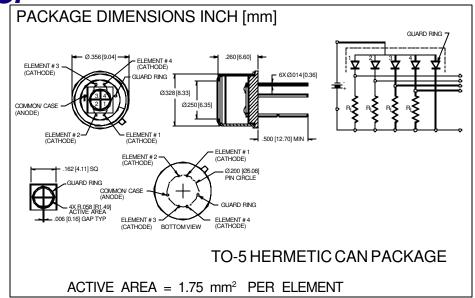




PHOTONIC DETECTORS INC.

1.06 Micron, High Speed Silicon Photodiode Quadrant Type PDI-M304





FEATURES

- .45 A/W @1060 nm
- 11 ns response time
- Low noise

DESCRIPTION

The **PDI-M304** is a high speed photodiode, processed on high resistivity P type silicon. Guard ring construction for enhanced 1060 nm response and 28 Mhz bandwidth. Packaged in a 6 leaded hermetic TO-5 hermetic package. Ideal for Nd YAG laser.

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

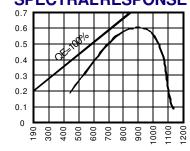
SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{ER}	Reverse Voltage		75	V
T_{STG}	Storage Temperature	-55	+125	∞
T _O	Operating Temperature Range	-40	+100	⊙C
T _s	Soldering Temperature*		+260	∘C
IL	Light Current		500	mA

^{*1/16} inch from case for 3 secs max

APPLICATIONS

- YAG laser detection
- Navigation
- Tracking and Aligning

SPECTRALRESPONSE



RESPONSIVITY (A/W)

WAVELENGTH(nm)

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
l ^{sc}	Short Circuit Current	H = 100 fc, 2850 K	49	52		μΑ
I _D	Dark Current	$H = 0, V_R = 200 V$		1.4	50	pA
R _{SH}	Shunt Resistance	$H = 0, V_R = 10 \text{ mV}$		-		MΩ
TCR _{SH}	RSH Temp. Coefficient	$H = 0, V_R = 10 \text{ mV}$		-10		% / °C
CJ	Junction Capacitance	$H = 0, V_R = 200 V^{**}$		1.2	1.4	рF
λrange	Spectral Application Range	Spot Scan	400		1150	nm
λр	Spectral Response - Peak	Spot Scan		900		nm
V _{BR}	Breakdown Voltage	I = 1 µ A	250	450		V
NEP	Noise Equivalent Power	V _R = 10 V @ 900 nm		1.5x10 ⁻¹¹		W/ √Hz
tr	Response Time	$RL = 50\Omega V_R = 200 V$		11		nS